



NPN Triple Diffused Planar Silicon Transistor

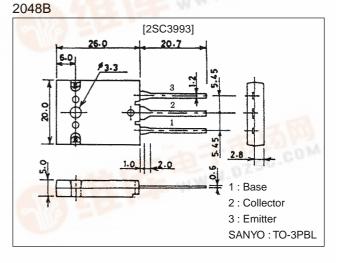


### **Features**

- · High breakdown voltage, high reliability.
- · Fast switching speed.
- · Wide ASO.
- · Adoption of MBIT process.

### Package Dimensions

unit:mm



# **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		1100	V
Collector-to-Emitter Voltage	VCEO		800	V
Emitter-to-Base Voltage	VEBO	100	7	V
Collector Current	IC		16	A
Collector Current (Pulse)	ICP	PW≤300µs, Duty cycle≤10%	40	А
Base Current	Ι <sub>Β</sub>		8	А
Collector Dissipation	PC	Tc=25°C	250	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	Ісво	V <sub>CB</sub> =800V, I <sub>E</sub> =0			10	μA
Emitter Cutoff Current	IEBO	V <sub>EB</sub> =5V, I <sub>C</sub> =0		-	10	μA
DC Current Gain	h <sub>FE</sub> 1	V <sub>CE</sub> =5V, I <sub>C</sub> =1.2A	10*	-5	40*	10.14
	h <sub>FE</sub> 2	V <sub>CE</sub> =5V, I <sub>C</sub> =6A	8	1.01	SC-	
Gain-Bandwidth Product	fT	V <sub>CE</sub> =10V, I <sub>C</sub> =1.2A	as W	15		MHz
Output Capacitance	Cob	V <sub>CB</sub> =10V, f=1MHz		320		pF

\* : The 2SC3993 are classified by 1.2A  $h_{FE}$  as follows : 10 K 20 15 L 30 20 M 40

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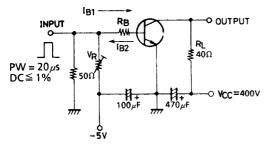
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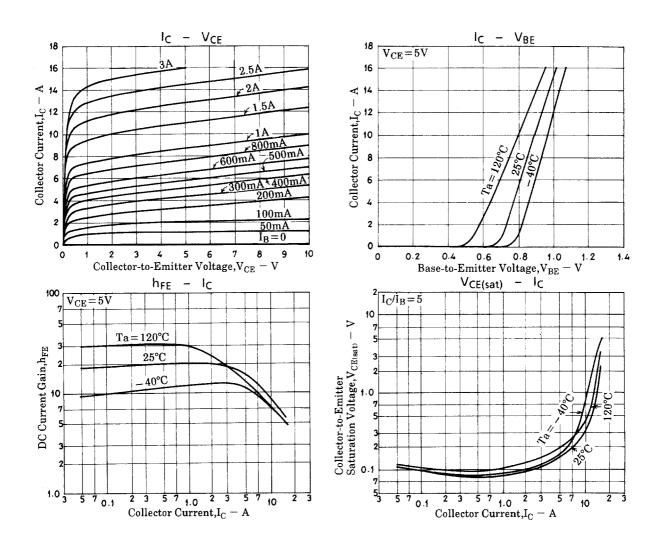
**SANYO Electric Co., Ltd. Semiconductor Bussiness Headquaters** TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

# 2SC3993

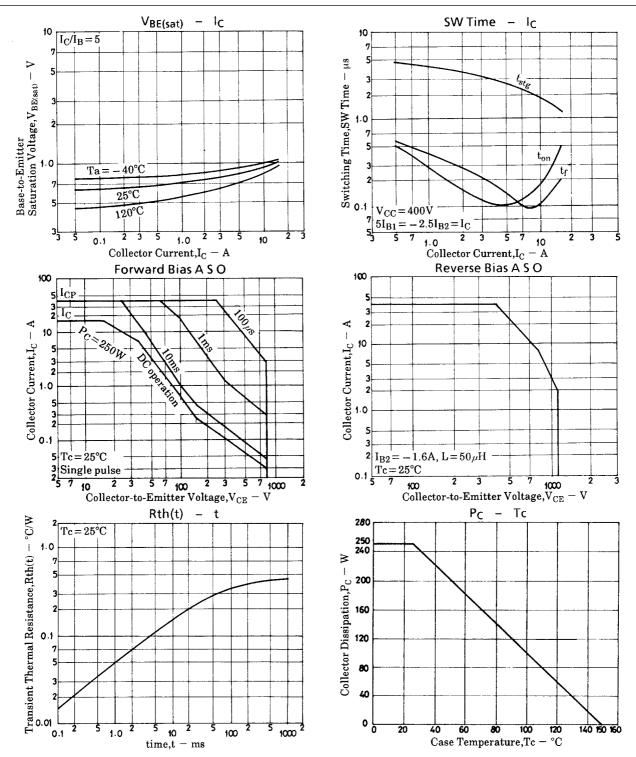
Parameter	Symbol	Conditions	Ratings			Unit
	Symbol		min	typ	max	Unit
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =6A, I <sub>B</sub> =1.2A			2.0	V
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =6A, I <sub>B</sub> =1.2A			1.5	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =1mA, I <sub>E</sub> =0	1100			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =10mA, R <sub>BE</sub> =∞	800			V
Emitter-to-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =1mA, I <sub>C</sub> =0	7			V
Collector-to-Emitter Sustain Voltage	V <sub>CEX(sus)</sub>	I <sub>C</sub> =8A, I <sub>B1</sub> =-I <sub>B2</sub> =-1.6A, L=500µH, clamped	800			V
Turn-ON Time	ton	$V_{CC}$ =400V, 5I <sub>B1</sub> =-2.5I <sub>B2</sub> =I <sub>C</sub> =10A, R <sub>L</sub> =40 $\Omega$			0.5	μs
Storage Time	tstg	$V_{CC}$ =400V, 5I <sub>B1</sub> =-2.5I <sub>B2</sub> =I <sub>C</sub> =10A, R <sub>L</sub> =40 $\Omega$			3.0	μs
Fall Time	t <sub>f</sub>	$V_{CC}$ =400V, 5I <sub>B1</sub> =-2.5I <sub>B2</sub> =I <sub>C</sub> =10A, R <sub>L</sub> =40 $\Omega$			0.3	μs

#### **Switching Time Test Circuit**





2SC3993



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